☐ XTAL1

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DIGITAL TV TUNER IC

Check for Samples: SN761645

FEATURES

- Integrated Mixer/Oscillator/PLL and IF GCA
- VHF-L, VHF-H, UHF 3-Band Local Oscillator
- RF AGC Detector Circuit
- I2C Bus Protocol
- Seven-Step Charge Pump Current
- Four NPN Emitter-Follower Type Band Switch Drivers
- One Auxiliary Port/5-Level ADC
- Programmable Reference Divider Ratio
- Crystal Oscillator 4-MHz/16-MHz Support
- Selectable Digital IFOUT and Analog IFOUT
- Standby Mode
- 5-V Power Supply
- 38-Pin TSSOP Package

APPLICATIONS

- Digital TV
- Digital CATV
- Set-Top Box

VLO OSC [☐ BS4 VHI OSC [☐ UHF RFIN1 37 UHF OSC1 [☐ UHF RFIN2 3 UHF OSC2 [4 VHI RFIN OSC GND ☐ VLO RFIN 34 ☐ RF GND CP \square 33 VTU 🖂 ☐ MIXOUT2 7 32 IF GND ☐ MIXOUT1 AIF OUT [☐ IFIN 30 DIF OUT1 F □ BUS GND 10 29 RF AGC OUT DIF OUT2 ___ 11 28 □ BS3 P5/ADC ___ 12 27 □ BS2 VCC \square 13 26 IF GCA IN1 ___ □ BS1 25 IF GCA IN2 [□ SDA 15 24 IF GCA CTRL □ 16 ☐ SCL 23 IF GCA GND □ 17 21 XTAL2 IF GCA OUT2 18

DBT PACKAGE

(TOP VIEW)

DESCRIPTION

The SN761645 is a low-phase-noise synthesized tuner IC designed for digital TV tuning systems. The circuit consists of a PLL synthesizer, three-band local oscillator and mixer, RF AGC detector circuit, and IF gain controlled amplifier, and is available in a small outline package.

IF GCA OUT1

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ORDERING INFORMATION

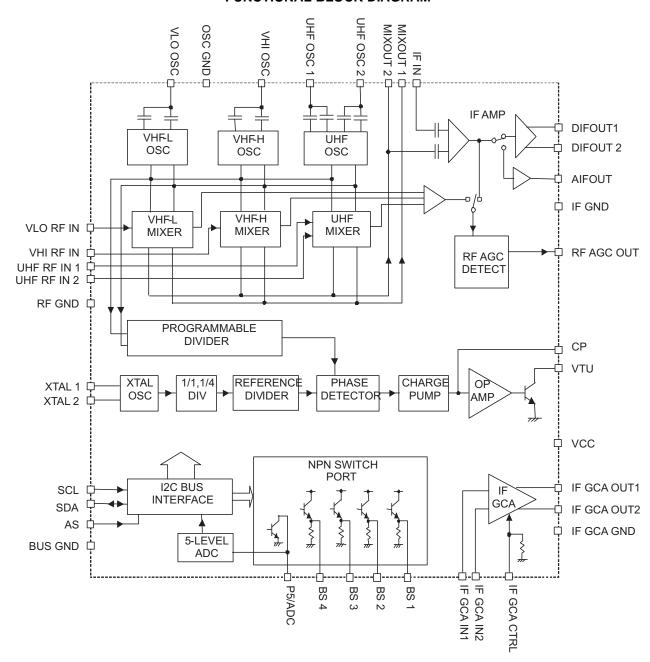
For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI web site at www.ti.com.

Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.





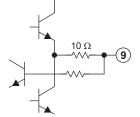
FUNCTIONAL BLOCK DIAGRAM

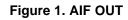




TERMINAL FUNCTIONS

TERMINA	SCHEMATIC		
NAME NO. AIF OUT 9		DESCRIPTION	SCHEWATIC
AIF OUT	9	IF amplifier output (unbalanced)	Figure 1
AS	22	Address selection input (open or connection to GND)	Figure 2
BS1	25	Band-switch 1 output (emitter follower)	Figure 3
BS2	26	Band-switch 2 output (emitter follower)	Figure 3
BS3	27	Band-switch 3 output (emitter follower)	Figure 3
BS4	38	Band-switch 4 output (emitter follower)	Figure 3
BUS GND	29	BUS ground	
СР	6	Charge pump output	Figure 4
DIF OUT1	10	IF amplifier balance output 1	Figure 5
DIF OUT2	11	IF amplifier balance output 2	Figure 5
IF GCA CTRL	16	IF GCA control voltage input	Figure 6
IF GCA GND	17	IF GCA ground	
IF GCA IN1	14	IF GCA input 1	Figure 7
IF GCA IN2	15	IF GCA input 2	Figure 7
IF GCA OUT1	19	IF GCA output 1	Figure 8
IF GCA OUT2	18	IF GCA output 2	Figure 8
IF GND	8	IF ground	
IF IN	30	IF amplifier input	Figure 9
MIX OUT1	31	Mixer output 1	Figure 10
MIX OUT2	32	Mixer output 2	Figure 10
OSC GND	5	Oscillator ground	
P5/ADC	12	Port-5 output/ADC input	Figure 11
RF AGC OUT	28	RF AGC output	Figure 12
RF GND	33	RF ground	
SCL	23	Serial clock input	Figure 13
SDA	24	Serial data input/output	Figure 14
UHF OSC1	3	UHF oscillator 1	Figure 15
UHF OSC2	4	UHF oscillator 2	Figure 15
UHF RF IN1	37	UHF RF input 1	Figure 16
UHF RF IN2	36	UHF RF input 2	Figure 16
VCC	13	Supply voltage	
VHI OSC	2	VHF HIGH oscillator	Figure 17
VHI RF IN	35	VHF HIGH RF input	Figure 18
VLO OSC	1	VHF LOW oscillator	Figure 19
VLO RF IN	34	VHF LOW RF input	Figure 20
VTU	7	Tuning voltage amplifier output	Figure 21
XTAL1	20	Crystal oscillator	Figure 22
XTAL2	21	Crystal oscillator	Figure 22





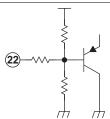


Figure 2. AS



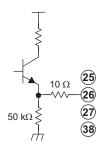


Figure 3. BS1, BS2, BS3, BS4

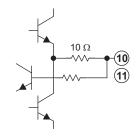


Figure 5. DIF OUT1, DIF OUT2

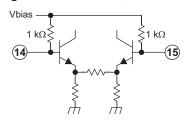


Figure 7. IF GCA IN1, IF GCA IN2

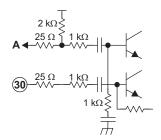


Figure 9. IF IN

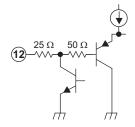


Figure 11. P5/ADC

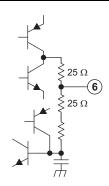


Figure 4. CP

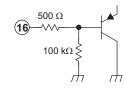


Figure 6. IF GCA CTRL

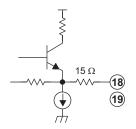


Figure 8. IF GCA OUT1, IF GCA OUT2

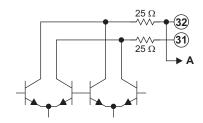


Figure 10. MIXOUT1, MIXOUT2

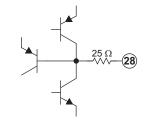


Figure 12. RF AGC OUT



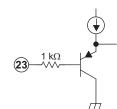


Figure 13. SCL

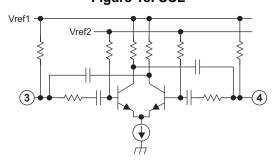


Figure 15. UHF OSC 1, UHF OSC 2

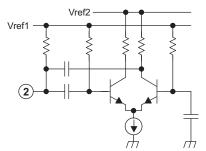


Figure 17. VHI OSC

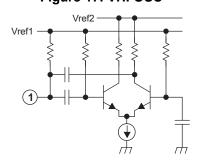


Figure 19. VLO OSC

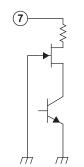


Figure 21. VTU

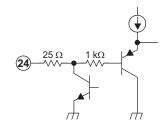


Figure 14. SDA

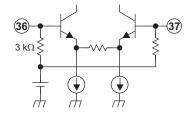


Figure 16. UHF RF IN1, UHF RF IN2

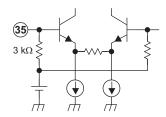


Figure 18. VHI RF IN

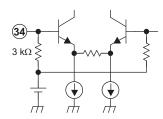


Figure 20. VLO RF IN

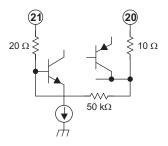


Figure 22. XTAL1, XTAL2



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over recommended operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V _{CC}	Supply voltage range (2)	V _{CC}	-0.4	6.5	V
V_{GND}	Input voltage range 1 (2)	RF GND, OSC GND, BUS GND	-0.4	0.4	V
VTU	Input voltage range 2 (2)	VTU	-0.4	35	V
V _{IN}	Input voltage range 3 (2)	Other pins	-0.4	6.5	V
P_D	Continuous total dissipation (3)	T _A ≤ 25°C		1277	mW
T _A	Operating free-air temperature range		-20	85	°C
T _{stg}	Storage temperature range		-65	150	°C
T_J	Maximum junction temperature			150	°C
t _{SC(max})	Maximum short-circuit time	Each pin to V _{CC} or to GND		10	s

Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

RECOMMENDED OPERATING CONDITIONS

			MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage	V _{CC}	4.5	5	5.3	٧
VTU	Tuning supply voltage	VTU		30	33	٧
I _{BS}	Output current of band switch	BS1 to BS4, one band switch on			10	mA
I _{P5}	Output current of port 5	P5			- 5	mA
T_A	Operating free-air temperature	•	-20		85	ů



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

IF IN1, MIX OUT 1, and MIX OUT 2 (pins 30, 31, and 32, respectively) withstand 1.5 kV, and all other pins withstand 2 kV, according to the Human-Body Model (1.5 k Ω , 100 pF).

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Voltage values are with respect to the IF GND of the circuit. Derating factor is 10.2 mW/°C for $T_A > 25$ °C.



ELECTRICAL CHARACTERISTICS

Total Device and Serial Interface

 V_{CC} = 4.5 V to 5.3 V, T_A = -20°C to 85°C (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
I _{CC} 1	Supply current 1	BS[1:4] = 0100, IFGCA disabled		90		mA
I _{CC} 2	Supply current 2	BS[1:4] = 0100, IFGCA enabled		110		mA
I _{CC-STBY}	Standby supply current	BS[1:4] = 1100		9		mA
V _{IH}	High-level input voltage (SCL, SDA)		2.3			V
V_{IL}	Low-level input voltage (SCL, SDA)				1.05	٧
I _{IH}	High-level input current (SCL, SDA)				10	μΑ
I _{IL}	Low-level input current (SCL, SDA)		-10			μA
V _{POR}	Power-on-reset supply voltage (threshold of supply voltage between reset and operation mode)		2.1	2.8	3.5	V
I ² C Interfa	ice					
V_{ADC}	ADC input voltage	See Table 11	0		V _{CC}	V
I _{ADH}	ADC high-level input current	$V_{ADC} = V_{CC}$			10	μΑ
I _{ADL}	ADC low-level input current	V _{ADC} = 0 V	-10			μA
V _{OL}	Low-level output voltage (SDA)	V _{CC} = 5 V, I _{OL} = 3 mA			0.4	V
I _{SDAH}	High-level output leakage current (SDA)	V _{SDA} = 5.3 V			10	μΑ
f _{SCL}	Clock frequency (SCL)			100	400	kHz
t _{HD-DAT}	Data hold time	See Figure 23	0		3.45	μs
t _{BUF}	Bus free time		1.3			μs
t _{HD-STA}	Start hold time		0.6			μs
t_{LOW}	SCL-low hold time		1.3			μs
t _{HIGH}	SCL-high hold time		0.6			μs
t _{SU-STA}	Start setup time		0.6			μs
t _{SU-DAT}	Data setup time		0.1			μs
t _r	Rise time (SCL, SDA)				1	μs
t _f	Fall time (SCL, SDA)				0.3	μs
t _{SU-STO}	Stop setup time		0.6			μs

Product Folder Link(s): SN761645



PLL and Band Switch

 V_{CC} = 4.5 V to 5.3 V, T_A = -20°C to 85°C (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
N	Divider ratio	15-bit frequency word	512		32767	
f _{XTAL}	Crystal oscillator frequency	$R_{XTAL} = 25 \Omega \text{ to } 300 \Omega$		4	16	MHz
Z_{XTAL}	Crystal oscillator input impedance	4-MHz crystal, V _{CC} = 5 V, T _A = 25°C		2		kΩ
V_{VTUL}	Tuning amplifier low-level output voltage	$R_L = 20 \text{ k}\Omega, \text{ VTU} = 33 \text{ V}$	0.2	0.45	0.6	V
I _{VTUOFF}	Tuning amplifier leakage current	Tuning amplifier = off, VTU = 33 V			10	μΑ
I _{CP000}		CP[2:0] = 000		35		
I _{CP001}		CP[2:0] = 001		70		
I _{CP010}		CP[2:0] = 010		140		
I _{CP011}	Charge-pump current	CP[2:0] = 011		210		μΑ
I _{CP100}		CP[2:0] = 100		280		
I _{CP101}		CP[2:0] = 101		350		
I _{CP110}		CP[2:0] = 110		420		
V_{CP}	Charge-pump output voltage	PLL locked		1.95		V
I _{CPOFF}	Charge-pump leakage current	V _{CP} = 2 V, T _A = 25°C	-15		15	nA
I _{BS}	Band switch driver output current (BS1-BS4)				10	mA
V _{BS1}	Bond switch driver output vallege (BC4 BC4)	I _{BS} = 10 mA	2.9			W
V _{BS2}	Band switch driver output voltage (BS1–BS4)	I _{BS} = 10 mA, V _{CC} = 5 V, T _A = 25°C	3.4	3.6		V
I _{BSOFF}	Band switch driver leakage current (BS1–BS4)	V _{BS} = 0 V			8	μΑ
I _{P5}	Band switch port sink current (P5/ADC)		-5			mA
V _{P5ON}	Band switch port output voltage (P5/ADC)	$I_{P5} = -2 \text{ mA}, V_{CC} = 5 \text{ V}, T_A = 25 ^{\circ}\text{C}$			0.6	٧

RF AGC⁽¹⁾

 V_{CC} = 5 V, T_A = 25°C, measured in Figure 24 reference measurement circuit at 50- Ω system, IF = 36.15 MHz (unless otherwise noted)

PARAMETER		TE	MIN	TYP	MAX	UNIT	
I _{OAGC0}	DE ACC output course current	ATC = 0			300		nA
I _{OAGC1}	RF AGC output source current	ATC = 1			9		μΑ
I _{OAGCSINK}	RF AGC peak sink current	ATC = 0	ATC = 0				μA
V _{OAGCH}	RFAGCOUT output high voltage (max level)	ATC = 1		3.7	4.2	4.7	V
V _{OAGCL}	RFAGCOUT output low voltage (min level)	ATC = 1			0.3		V
V _{AGCSP00}			ATP[2:0] = 000		114		
V _{AGCSP01}			ATP[2:0] = 001		112		
V _{AGCSP02}			ATP[2:0] = 010		110		
V _{AGCSP03}	Start-point IF output level	AISL = 0	ATP[2:0] = 011		108		dΒμV
V _{AGCSP04}			ATP[2:0] = 100		106		
V _{AGCSP05}			ATP[2:0] = 101		104		
V _{AGCSP06}			ATP[2:0] = 110		102		

(1) When AISL = 1, RF AGC function is not available at VHF-L band.

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Mixer, Oscillator, IF Amplifier (DIF OUT)

 $V_{CC} = 5 \text{ V}$, $T_A = 25^{\circ}\text{C}$, measured in Figure 24 reference measurement circuit at 50- Ω system, IF = 36.15 MHz (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN TYP MAX	UNIT
GC _{1D}	Conversion sain (mixer, IF amplifier) \//IF LOW	$f_{IN} = 50.85 \text{ MHz}^{(1)}$	35	dB
GC _{3D}	Conversion gain (mixer - IF amplifier), VHF-LOW	f _{IN} = 149.85 MHz ⁽¹⁾	35	dB
GC _{4D}	Conversion sain (mixer, IF amplifier) \//IF LIICH	f _{IN} = 156.85 MHz ⁽¹⁾	35	dB
GC _{6D}	Conversion gain (mixer - IF amplifier), VHF-HIGH	$f_{IN} = 425.85 \text{ MHz}^{(1)}$	35	dB
GC _{7D}	Conversion gain (mixer - IF amplifier), UHF	$f_{IN} = 433.85 \text{ MHz}^{(1)}$	35	dB
GC _{9D}	Conversion gain (mixer - in ampliner), or in	$f_{IN} = 857.85 \text{ MHz}^{(1)}$	35	dB
NF _{1D}	Noise figure, VHF-LOW	f _{IN} = 50.85 MHz	9	dB
NF _{3D}	Noise ligule, VHF-LOW	f _{IN} = 149.85 MHz	9	dB
NF _{4D}	Noise figure, VHF-HIGH	f _{IN} = 156.85 MHz	9	dB
NF _{6D}	Noise ligure, VIII - HIGH	f _{IN} = 425.85 MHz	10	dB
NF _{7D}	Noise figure, UHF	f _{IN} = 433.85 MHz	10	dB
NF _{9D}	Noise ligure, of in	f _{IN} = 857.85 MHz	11	dB
CM _{1D}	Input voltage causing 1% cross modulation distortion,	$f_{IN} = 50.85 \text{ MHz}^{(2)}$	92	dΒμV
CM _{3D}	VHF-LOW	f _{IN} = 149.85 MHz ⁽²⁾	92	dΒμV
CM _{4D}	Input voltage causing 1% cross modulation distortion,	f _{IN} = 156.85 MHz ⁽²⁾	92	dΒμV
CM _{6D}	VHF-HIGH	$f_{IN} = 425.85 \text{ MHz}^{(2)}$	92	dΒμV
CM _{7D}	Input voltage causing 1% cross modulation distortion, UHF	$f_{IN} = 433.85 \text{ MHz}^{(2)}$	92	dΒμV
CM _{9D}	input voltage causing 1% cross modulation distortion, or in	$f_{IN} = 857.85 \text{ MHz}^{(2)}$	92	dΒμV
V _{IFO1D}	IF output voltage, VHF-LOW	f _{IN} = 50.85 MHz	117	dΒμV
V _{IFO3D}	iii output voitage, vriii -LOvv	f _{IN} = 149.85 MHz	117	dΒμV
V _{IFO4D}	│ │ IF output voltage, VHF-HIGH	f _{IN} = 156.85 MHz	117	dΒμV
V _{IFO6D}	11 Output voltage, VIII -IIIOII	f _{IN} = 425.85 MHz	117	dΒμV
V _{IFO7D}	☐ IF output voltage, UHF	f _{IN} = 433.85 MHz	117	dΒμV
V _{IFO9D}	ir output voltage, or ir	f _{IN} = 857.85 MHz	117	dΒμV
Φ _{PLVL1D}	Phase noise, VHF-LOW	$f_{IN} = 50.85 \text{ MHz}^{(3)}$	-92	dBc/Hz
Φ _{PLVL3D}	I Hase Holse, VIII -LOVV	f _{IN} = 149.85 MHz ⁽⁴⁾	-91	dBc/Hz
Φ _{PLVL4D}	Phase noise, VHF-HIGH	f _{IN} = 156.85 MHz ⁽³⁾	-86	dBc/Hz
Φ _{PLVL6D}	FIIASE HUISE, VIIF-IIIGII	f _{IN} = 425.85 MHz ⁽⁴⁾	-83	dBc/Hz
Φ _{PLVL7D}	Phase paice TIHE	f _{IN} = 433.85 MHz ⁽³⁾	-79	dBc/Hz
Φ _{PLVL9D}	Phase noise, UHF	f _{IN} = 857.85 MHz ⁽⁴⁾	-77	dBc/Hz

⁽¹⁾ RF input level = 70 dB μ V, differential output (2) f_{undes} = f_{des} \pm 7 MHz, Pin = 70 dB μ V, AM 1 kHz, 30%, DES/CM = S/I = 46 dB (3) Offset = 1 kHz, CP current = 70 μ A, reference divider = 24 (4) Offset = 1 kHz, CP current = 420 μ A, reference divider = 24



Mixer, Oscillator, IF Amplifier (AIF OUT)

 V_{CC} = 5 V, T_A = 25°C, measured in Figure 24 reference measurement circuit at 50- Ω system, IF = 36.15 MHz (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN TYP MAX	UNIT
GC _{1A}	Conversion sain (mixer, IF amplifier) \/\IF I O\/	f _{IN} = 50.85 MHz ⁽¹⁾	29	dB
GC _{3A}	Conversion gain (mixer - IF amplifier), VHF-LOW	f _{IN} = 149.85 MHz ⁽¹⁾	29	dB
GC _{4A}	Conversion rain (with a UF annulfied) \/\UF UF	f _{IN} = 156.85 MHz ⁽¹⁾	29	dB
GC _{6A}	Conversion gain (mixer - IF amplifier), VHF-HIGH	f _{IN} = 425.85 MHz ⁽¹⁾	29	dB
GC _{7A}	Conversion sain (mixer, IF amplifier) IIIIF	f _{IN} = 433.85 MHz ⁽¹⁾	29	dB
GC _{9A}	Conversion gain (mixer - IF amplifier), UHF	f _{IN} = 857.85 MHz ⁽¹⁾	29	dB
NF _{1A}	Noise figure VIII LOW	f _{IN} = 50.85 MHz	9	dB
NF _{3A}	Noise figure, VHF-LOW	f _{IN} = 149.85 MHz	9	dB
NF _{4A}	Noise figure, VHF-HIGH	f _{IN} = 156.85 MHz	9	dB
NF _{6A}	Noise ligule, VHF-HIGH	f _{IN} = 425.85 MHz	10	dB
NF _{7A}	Noise figure LIHE	f _{IN} = 433.85 MHz	10	dB
NF _{9A}	Noise figure, UHF	f _{IN} = 857.85 MHz	11	dB
CM _{1A}	Input voltage causing 1% cross modulation distortion,	$f_{IN} = 50.85 \text{ MHz}^{(2)}$	87	dΒμV
CM _{3A}	VHF-LOW	f _{IN} = 149.85 MHz ⁽²⁾	87	dΒμV
CM _{4A}	Input voltage causing 1% cross modulation distortion,	f _{IN} = 156.85 MHz ⁽²⁾	87	dΒμV
CM _{6A}	VHF-HIGH	f _{IN} = 425.85 MHz ⁽²⁾	87	dΒμV
CM _{7A}	Input voltage equaing 19/ gross modulation distortion LIHE	$f_{IN} = 433.85 \text{ MHz}^{(2)}$	87	dΒμV
CM _{9A}	Input voltage causing 1% cross modulation distortion, UHF	f _{IN} = 857.85 MHz ⁽²⁾	87	dΒμV
V _{IFO1A}	IF output voltage, VHF-LOW	f _{IN} = 50.85 MHz	117	dΒμV
V _{IFO3A}	iii output voitage, vriii -LOvv	f _{IN} = 149.85 MHz	117	dΒμV
V _{IFO4A}	│ │ IF output voltage, VHF-HIGH	f _{IN} = 156.85 MHz	117	dΒμV
V _{IFO6A}	output voltage, viii -iiiGii	f _{IN} = 425.85 MHz	117	dΒμV
V _{IFO7A}	F output voltage, UHF	f _{IN} = 433.85 MHz	117	dΒμV
V _{IFO9A}	ir output voltage, onr	f _{IN} = 857.85 MHz	117	dΒμV
Φ _{PLVL1A}	Phase noise, VHF-LOW	$f_{IN} = 50.85 \text{ MHz}^{(3)}$	-92	dBc/Hz
Φ _{PLVL3A}	T Hase Holse, VIII -LOVV	f _{IN} = 149.85 MHz ⁽³⁾	-96	dBc/Hz
Φ _{PLVL4A}	Phase noise, VHF-HIGH	f _{IN} = 156.85 MHz ⁽³⁾	-85	dBc/Hz
Φ _{PLVL6A}	Filase Hoise, VIIF-IIIOII	f _{IN} = 425.85 MHz ⁽³⁾	-88	dBc/Hz
Φ _{PLVL7A}	Phase noise, UHF	f _{IN} = 433.85 MHz ⁽³⁾	-80	dBc/Hz
Φ _{PLVL9A}	Fliase Hoise, UTIF	f _{IN} = 857.85 MHz ⁽³⁾	-85	dBc/Hz

⁽¹⁾ RF input level = $70 \text{ dB}\mu\text{V}$

 $f_{undes} = f_{des} \pm 7$ MHz, Pin = 70 dB μ V, AM 1 kHz, 30%, DES/CM = S/I = 46 dB Offset = 10 kHz, CP current = 35 μ A, reference divider = 64

IF Gain Controlled Amplifier

 V_{CC} = 5 V, T_A = 25°C, measured in Figure 24 reference measurement circuit at 50- Ω system, IF = IF = 36.15 MHz (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
I _{IFGCA}	Input current (IF GCA CTRL)	V _{IFGCA} = 3 V		60	90	μΑ
$V_{IFGCAMAX}$	Maximum gain control voltage	Gain maximum	3		V_{CC}	V
V _{IFGCAMIN}	Minimum gain control voltage	Gain minimum	0		0.2	V
G _{IFGCAMAX}	Maximum gain	V _{IFGCA} = 3 V		67		dB
G _{IFGCAMIN}	Minimum gain	V _{IFGCA} = 0 V		3		dB
GCR _{IFGCA}	Gain control range	V _{IFGCA} = 0 V to 3 V		64		dB
V _{IFGCAOUT}	Output voltage	Single-ended output, V _{IFGCA} = 3 V		2.1		Vpp
NF _{IFGCA}	Noise figure	V _{IFGCA} = 3 V		11		dB
IM3 _{IFGCA}	Third order intermodulation distortion	$ f_{IFGCAIN1} = 35.65 \text{ MHz}, \\ f_{IFGCAIIN2} = 36.65 \text{ MHz}, \\ V_{IFGCAOUT} = -2 \text{ dBm}, \\ V_{IFGCA} = 3 \text{ V} $		-50		dBc
IIP _{3IFGCA}	Input intercept point	V _{IFGCA} = 0 V		11		dBm
R _{IFGCAIN}	Input resistance (IF GCA IN1, IF GCA IN2)			1		kΩ
R _{IFGCAOUT}	Output resistance (IF GCA OUT1, IF GCA OUT2)			25		Ω



FUNCTIONAL DESCRIPTION

I²C Bus Mode

I^2C Write Mode (R/ $\overline{W} = 0$)

Table 1. Write Data Format

	MSB							LSB	
Address Byte (ADB)	1	1	0	0	0	0	MA	R/W = 0	A ⁽¹⁾
Divider Byte 1 (DB1)	0	N14	N13	N12	N11	N10	N9	N8	A ⁽¹⁾
Divider Byte 2 (DB2)	N7	N6	N5	N4	N3	N2	N1	N0	A ⁽¹⁾
Control Byte 1 (CB1)	1	0	ATP2	ATP1	ATP0	RS2	RS1	RS0	A ⁽¹⁾
Band Switch Byte (BB)	CP1	CP0	AISL	P5	BS4	BS3	BS2	BS1	A ⁽¹⁾
Control Byte 2 (CB2)	1	1	ATC	MODE	DISGCA	IFDA	CP2	IXD4	A ⁽¹⁾

(1) A = acknowledge

Table 2. Write Data Symbol Description

SYMBOL	DESCRIPTION	DEFAULT
	Address set bit	
MA	MA = 0 : AS pin = 0 V (connection to GND)	
	MA = 1 : AS pin = Open	
NI[4.4.0]	Programmable counter set bits	N14 = N13 = N12 = = N0 = 0
N[14:0]	$N = N14 \times 2^{14} + N13 \times 2^{13} + + N1 \times 2 + N0$	N14 = N13 = N12 = = N0 = 0
ATP[2:0]	RF AGC start-point control bits (see Table 3)	ATP[2:0] = 000
RS[2:0]	Reference divider ratio-selection bits (see Table 4)	RS[2:0] = 000
CP[2:0]	Charge-pump current set bits (see Table 5)	CP[2:0] = 000
	Port output / ADC input control bit	
P5	P5 = 0 : ADC input	P5 = 0
	P5 = 1 : Tr = ON	
	Band-switch driver output control bits	
	BSn = 0: $Tr = OFF$	
	BSn = 1: Tr = ON	
	Band selection and standby function control bits	
BS[4:1]	BS2 BS1	BS[4:1] = 0000
	0 1 VHF-LO	
	1 0 VHF-HI	
	0 0 UHF	
	1 1 Standby mode / stop MOP function	
	RFAGC output current-set bit	
ATC	ATC = 0: Source current = 300nA	ATC = 0
	ATC = 1: Source current = 9uA	
	Device mode selection bit	
MODE	MODE = 0 : Test mode	MODE = 0
	MODE = 1 : Normal operation	
	Other control bits	
DISGCA	DISGCA IF GCA control bit (see Table 6)	DISGCA = 0
IFDA	IFDA AIF/DIF OUT selection bit (see Table 7)	IFDA = 0
AISL	AISL RFAGC detector input selection bit (see Table 8)	AISL = 0
IXD4	IXD4 Reference divider control bit (see Table 4)	IXD4 = 0

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Table 3. RF AGC Start Point

MODE	ATDO	ATD4	ATDO	IFOUT	LEVEL
MODE	ATP2	ATP1	ATP0	(dBµV)	(mVp-p)
1	0	0	0	114	1417
1	0	0	1	112	1126
1	0	1	0	110	894
1	0	1	1	108	710
1	1	0	0	106	564
1	1	0	1	104	448
1	1	1	0	102	356
1	1	1	1	Disa	abled

Table 4. Reference Divider Ratio

MODE	IXD4	RS2	RS1	RS0	REFERENCE DIVIDER RATIO
1	0	0	0	0	96
1	0	0	0	1	112
1	0	0	1	0	128
1	0	0	1	1	256
1	0	1	0	0	512
1	0	1	0	1	320
1	1	0	0	0	24
1	1	0	0	1	28
1	1	0	1	0	32
1	1	0	1	1	64
1	1	1	0	0	128
1	1	1	0	1	80
1	Х	1	1	1	Forbidden

Table 5. Charge-Pump Current

MODE	CP2	CP1	CP0	CHARGE PUMP CURRENT (μΑ)
1	0	0	0	35
1	0	0	1	70
1	0	1	0	140
1	0	1	1	210
1	1	0	0	280
1	1	0	1	350
1	1	1	0	420
1	1	1	1	Forbidden

Table 6. IF GCA Control

MODE	DISGCA	IF GCA FUNCTION
1	0	IF GCA enabled
1	1	IF GCA disabled

Table 7. AIF / DIF OUT Selection

MODE	IFDA	IF OUT FUNCTION
1	0	DIF OUT 1,2 selected
1	1	AIF OUT selected

Table 8. RF AGC Detector Input Selection

MODE	AISL	RF AGC DETECTOR INPUT
1	0	IF amplifier selected
1	1 ⁽¹⁾	Mixer selected

(1) When AISL = 1, RF AGC function is not available at VHF-L band (output level is undefined).

I^2C Read Mode (R/ $\overline{W} = 1$)

Table 9. Read Data Format

	MSB							LSB	
Address byte (ADB)	1	1	0	0	0	0	MA	$R/\overline{W} = 1$	A ⁽¹⁾
Status byte (SB)	POR	FL	1	1	1	A2	A1	A0	_

(1) A = acknowledge

Table 10. Read Data Symbol Description

SYMBOL	DESCRIPTION	DEFAULT
MA	Address set bit	
	MA = 0 : VLO OSC/AS pin = 0 V (connection to GND)	
	MA = 1 : VLO OSC/AS pin = Open	
POR	Power-on-reset flag	POR = 1
	POR set: power on POR reset: end-of-data transmission procedure	
FL	In-lock flag ⁽¹⁾	
	FL = 0 : PLL unlocked	
	FL = 1 : PLL locked	
A[2:0]	Digital data of ADC (see Table 11)	
	Bit P5 must be set to 0.	

⁽¹⁾ Lock detector works by using phase error pulse at the phase detector. Lock flag (FL) is set or reset according to this pulse-width disciminator. Hence, instability of the PLL may cause the lock detection circuit to malfunction. To stablize the PLL, it is required to evaluate application circuit in various condition of loop-gain (loop filter, CP current) and to verify under operation of the actual application.

Table 11. ADC Level (1)

A2	A 1	Α0	VOLTAGE APPLIED ON ADC INPUT
1	0	0	0.6 V _{CC} to V _{CC}
0	1	1	0.45 V _{CC} to 0.6 V _{CC}
0	1	0	0.3 V _{CC} to 0.45 V _{CC}
0	0	1	0.15 V _{CC} to 0.3 V _{CC}
0	0	0	0 V to 0.15 V _{CC}

(1) Accuracy is $0.03 \times V_{CC}$.

Example I²C Data Write Sequences

Telegram examples:

Start - ADB - DB1 - DB2 - CB1 - BB - CB2 - Stop

Start - ADB - DB1 - DB2 - Stop

Start - ADB - CB1 - BB - CB2 - Stop

Start - ADB - CB1 - BB - Stop

Start - ADB - CB2 - Stop

Abbreviations:

ADB: Address byte BB: Band switch byte CB1: Control byte 1 CB2: Control byte 2 DB1: Divider byte 1 DB2: Divider byte 2 Start: Start condition Stop: Stop condition

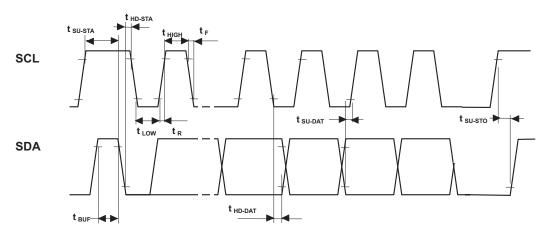
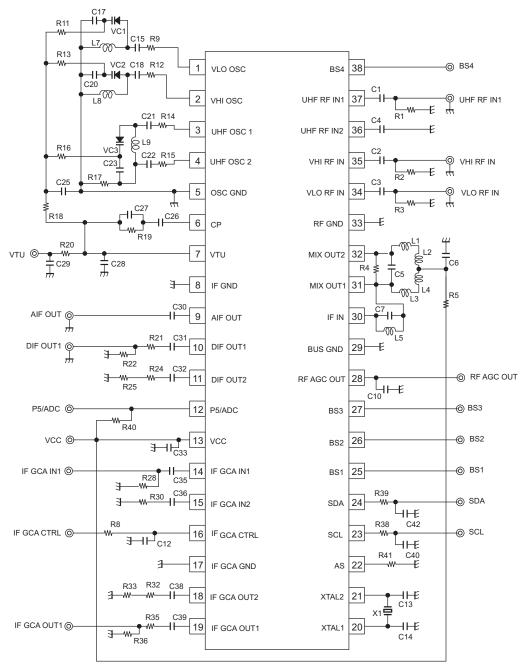


Figure 23. I²C Timing



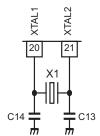
APPLICATION INFORMATION



NOTE: This application information is advisory and performance-check is required at actual application circuits. TI assumes no responsibility for the consequences of use of this circuit, such as an infringement of intellectual property rights or other rights, including patents, of third parties.

Figure 24. Reference Measurement Circuit





	Crystal X1	Capac	citors
Frequency	Туре	C13	C14
4 MHz	HC49SFNB04000H0 (Kyocera)	27 pF	27 pF
16 MHz	CX3225GB16000D0 (Kyocera)	14 pF	14 pF

Figure 25. Reference Crystal Oscillation Circuit

Table 12. Component Values for Measurement Circuit

PART NAME	VALUE	PART NAME	VALUE
C1 (UHF RFIN1)	2.2nF	R1 (UHF RFIN1)	Open (51Ω)
C2 (VHI RFIN)	2.2nF	R2 (VHI RFIN)	Open (51Ω)
C3 (VLO RFIN)	2.2nF	R3 (VLO RFIN)	Open (51Ω)
C4 (UHF RFIN)	2.2nF	R4 (MIXOUT)	Open
C5 (MIXOUT)	5.5pF	R5 (MIXOUT)	0Ω
C6 (MIXOUT)	2.2nF	R8 (IF GCA CTRL)	0Ω
C7 (IF IN)	0Ω	R9 (VLO OSC)	0Ω
C10 (RF AGC OUT)	0.15µF	R11 (VLO OSC)	3.3kΩ
C12 (IF GCA CTRL)	0.1µF	R12 (VHI OSC)	10Ω
C13 (XTAL2)	27pF	R13 (VHI OSC)	3.3kΩ
C14 (XTAL1)	27pF	R14 (UHF OSC)	4.7Ω
C15 (VLO OSC)	4pF	R15 (UHF OSC)	4.7Ω
C17 (VLO OSC)	68pF	R16 (UHF OSC)	1kΩ
C18 (VHI OSC)	10pF	R17 (UHF OSC)	2.2kΩ
C20 (VHI OSC)	130pF	R18 (VTU)	3.3kΩ
C21 (UHF OSC)	6pF	R19 (CP)	82kΩ
C22 (UHF OSC)	6pF	R20 (VTU)	22kΩ
C23 (UHF OSC)	20pF	R21 (DIF OUT1)	200Ω
C25 (VTU)	2.2nF/50V	R22 (DIF OUT1)	Open
C26 (CP)	3.9nF/50V	R24 (DIF OUT2)	200Ω
C27 (CP)	10pF/50V	R25 (DIF OUT2)	51Ω
C28 (VTU)	150pF/50V	R28 (IF GCA IN1)	(51Ω)
C29 (VTU)	2.2nF/50V	R30 (IF GCA IN2)	(0Ω)
C30 (AIF OUT)	2.2nF	R32 (IF GCA OUT2)	200Ω
C31 (DIF OUT1)	2.2nF	R33 (IF GCA OUT2)	51Ω
C32 (DIF OUT2)	2.2nF	R35 (IF GCA OUT1)	200Ω
C33 (VCC)	0.1µF	R36 (IF GCA OUT1)	Open
C35 (IF GCA IN1)	2.2nF	R38 (SCL)	330Ω
C36 (IF GCA IN2)	2.2nF	R39 (SDA)	330Ω
C38 (IF GCA OUT2)	2.2nF	R40 (P5)	Open
C39 (IF GCA OUT1)	2.2nF	R41 (AS)	Open
C40 (SCL)	Open		
C42 (SDA)	Open	VC1 (VLO OSC)	KDV270E
		VC2 (VHI OSC)	KDV270E
		VC3 (UHF OSC)	KDV216E
		X1	4MHz crystal



Table 12. Component Values for Measurement Circuit (continued)

PART NAME	VALUE	PART NAME
L1 (MIXOUT)	470nH (LK1608R47KT Taiyo Yuden)	
L2 (MIXOUT)	560nH (LK1608R56KT Taiyo Yuden)	
L3 (MIXOUT)	470nH (LK1608R47KT Taiyo Yuden)	
L4 (MIXOUT)	560nH (LK1608R56KT Taiyo Yuden)	
L5 (IFIN)	Open	
L7 (VLO OSC)	φ3.0mm, 9T, wire0.32mm	
L8 (VHI OSC)	φ1.8mm, 4T, wire0.4mm	
L9 (UHF OSC)	φ1.8mm, 2T, wire0.4mm	

IF frequency: 36 MHz

Local frequency range: VHF-LOW: 87 to 186 MHz

VHF-HIGH: 193 to 462 MHz UHF: 470 to 894 MHz

Test Circuits

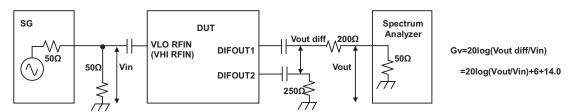


Figure 26. VHF Conversion Gain Measurement Circuit (at DIFOUT)

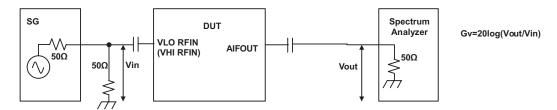


Figure 27. VHF Conversion Gain Measurement Circuit (at AIFOUT)

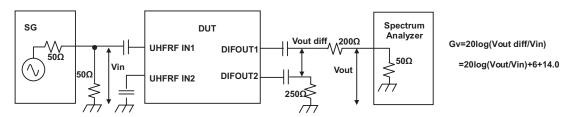


Figure 28. UHF Conversion Gain Measurement Circuit (at DIFOUT)

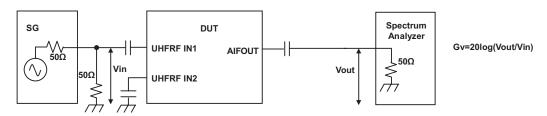


Figure 29. UHF Conversion Gain Measurement Circuit (at AIFOUT)

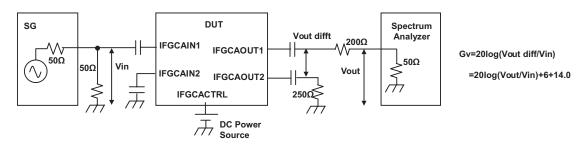


Figure 30. IF GCA Gain Measurement Circuit

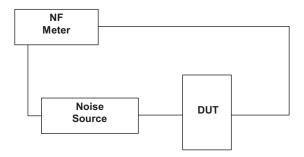


Figure 31. Noise Figure Measurement Circuit

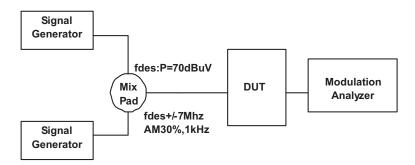


Figure 32. 1% Cross Modulation Distortion Measurement Circuit

TYPICAL CHARACTERISTICS

Band Switch Driver Output Voltage (BS1-BS4)

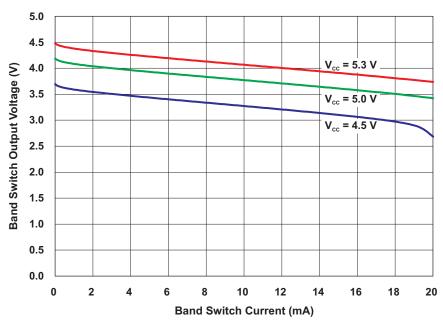


Figure 33. Band Switch Driver Output Voltage

S-Parameter

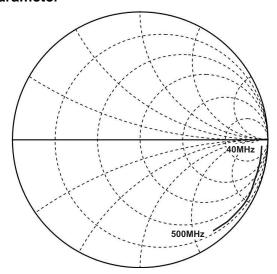


Figure 34. VLO, VHI RFIN

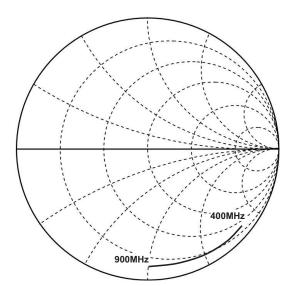


Figure 35. UHF RFIN





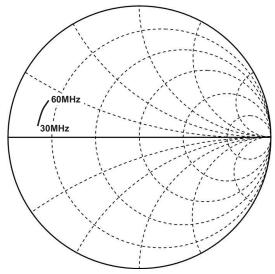


Figure 36. DIFOUT

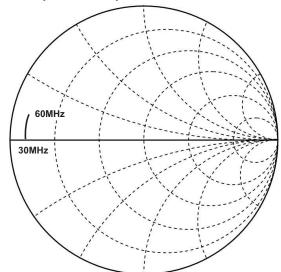


Figure 37. AIFOUT

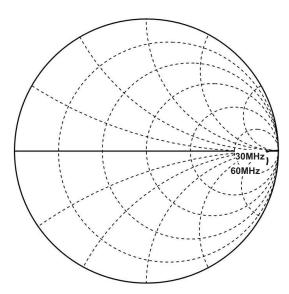


Figure 38. IF GCA IN

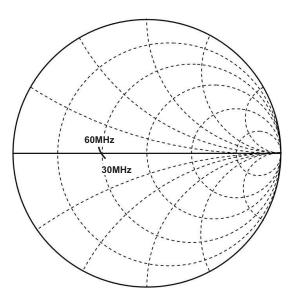


Figure 39. IF GCAOUT



TYPICAL CHARACTERISTICS (continued)

IF GCA Gain vs Control Voltage

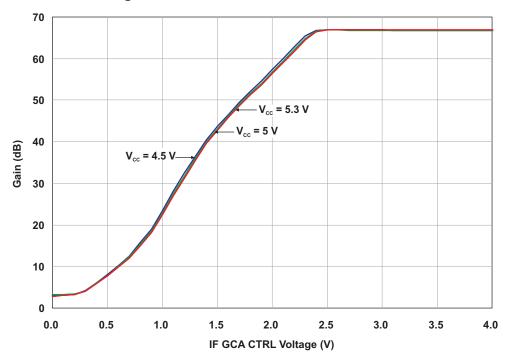


Figure 40. IF GCA Gain vs Control Voltage



PACKAGE OPTION ADDENDUM

10-Oct-2013

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)		(3)		(4/5)	
SN761645DBTR	OBSOLETE	TSSOP	DBT	38		TBD	Call TI	Call TI	-20 to 85	B1645	

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

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Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

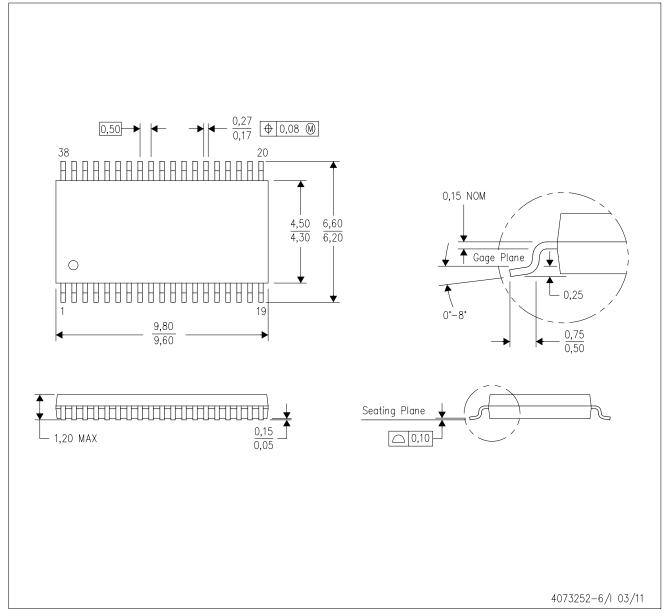
- (3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

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DBT (R-PDSO-G38)

PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion.
- D. Falls within JEDEC MO-153.



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